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Team Nexperia

BCM857BV; BCM857BS; BCM857DS

PNP/PNP matched double transistors

Rev. 06 — 28 August 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP matched double transistors in small Surface-Mounted Device (SMD) plastic packages. The transistors are fully isolated internally.

Table 1. Product overview

Type number	g-		NPN/NPN	Matched version of	
	NXP	JEITA	complement		
BCM857BV	SOT666	-	BCM847BV	BC857BV	
BCM857BS	SOT363	SC-88	BCM847BS	BC857BS	
BCM857DS	SOT457	SC-74	BCM847DS	-	

1.2 Features

- Current gain matching
- Base-emitter voltage matching
- Drop-in replacement for standard double transistors

1.3 Applications

- Current mirror
- Differential amplifier

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
V_{CEO}	collector-emitter voltage	open base	-	-	-45	V
I _C	collector current		-	-	-100	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	200	290	450	



Table 2. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device						
h _{FE1} /h _{FE2}	h _{FE} matching	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	[1] 0.9	1	-	
$V_{BE1}-V_{BE2}$	V _{BE} matching	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	[2] -	-	2	mV

^[1] The smaller of the two values is taken as the numerator.

2. Pinning information

Table 3. Pinning

	9		
Pin	Description	Simplified outline	Symbol
1	emitter TR1		
2	base TR1	[6] [5] [4]	6 5 4
3	collector TR2		TR2
4	emitter TR2		(TR1)
5	base TR2		
6	collector TR1	001aab555	1 2 3
			sym018

3. Ordering information

Table 4. Ordering information

Type number	per Package							
	Name	Description	Version					
BCM857BV	-	plastic surface-mounted package; 6 leads	SOT666					
BCM857BS	SC-88	plastic surface-mounted package; 6 leads	SOT363					
BCM857DS	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457					

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
BCM857BV	3B
BCM857BS	A9*
BCM857DS	R8

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

^[2] The smaller of the two values is subtracted from the larger value.

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-45	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT666		[1][2]	200	mW
	SOT363		[1] -	200	mW
	SOT457		<u>[1]</u> _	250	mW
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT666		[1][2] _	300	mW
	SOT363		[1] -	300	mW
	SOT457		[1] -	380	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT666		[1][2]	-	625	K/W
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT457		<u>[1]</u> _	-	500	K/W

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^[2] Reflow soldering is the only recommended soldering method.

 Table 7.
 Thermal characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device	9					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT666		[1][2] _	-	416	K/W
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT457		<u>[1]</u> _	-	328	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V};$ $I_E = 0 \text{ A}$	-	-	-15	nA
		$V_{CB} = -30 \text{ V};$ $I_{E} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$	-	-	– 5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V};$ $I_{C} = 0 \text{ A}$	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \mu\text{A}$	-	250	-	
		$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	200	290	450	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -0.5 \text{ mA}$	-	- 50	-200	mV
		$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$	-	-200	-400	mV
V _{BEsat}	base-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	<u>[1]</u> -	-760	-	mV
		$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$	<u>[1]</u> _	-920	-	mV
V_{BE}	base-emitter voltage	$V_{CE} = -5 \text{ V};$ $I_C = -2 \text{ mA}$	<u>[2]</u> –600	-650	-700	mV
		$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA}$	[2] -	-	-760	mV
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.2	pF
C _e	emitter capacitance	$V_{EB} = -0.5 \text{ V};$ $I_{C} = i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	10	-	pF

Table 8. Characteristics ...continued $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified

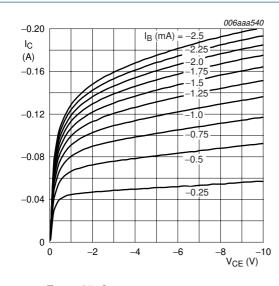
ramb = 0 dames cancer operated							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
f _T	transition frequency	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA};$ $f = 100 \text{ MHz}$	100	175	-	MHz	
NF	noise figure	$V_{CE} = -5 \text{ V};$ $I_{C} = -0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega;$ $f = 10 \text{ Hz to}$ 15.7 kHz	-	1.6	-	dB	
		$\begin{split} &V_{CE} = -5 \text{ V};\\ &I_{C} = -0.2 \text{ mA};\\ &R_{S} = 2 \text{ k}\Omega;\\ &f = 1 \text{ kHz};\\ &B = 200 \text{ Hz} \end{split}$	-	3.1	-	dB	
Per device							
h _{FE1} /h _{FE2}	h _{FE} matching	$V_{CE} = -5 \text{ V};$ $I_C = -2 \text{ mA}$	[3] 0.9	1	-		
$V_{BE1}-V_{BE2}$	V _{BE} matching	$V_{CE} = -5 \text{ V};$ $I_C = -2 \text{ mA}$	<u>[4]</u> _	-	2	mV	

^[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

^[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

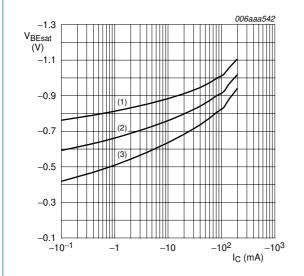
^[3] The smaller of the two values is taken as the numerator.

^[4] The smaller of the two values is subtracted from the larger value.



 $T_{amb} = 25 \, ^{\circ}C$

Fig 1. Collector current as a function of collector-emitter voltage; typical values



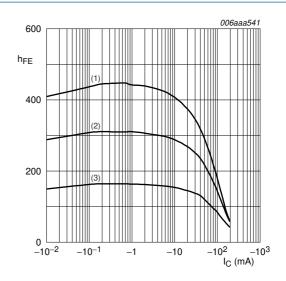
 $I_{\rm C}/I_{\rm B} = 20$

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 3. Base-emitter saturation voltage as a function of collector current; typical values



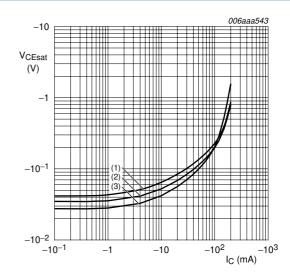
 $V_{CE} = -5 \text{ V}$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 2. DC current gain as a function of collector current; typical values



 $I_C/I_B = 20$

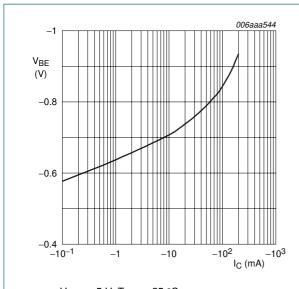
(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

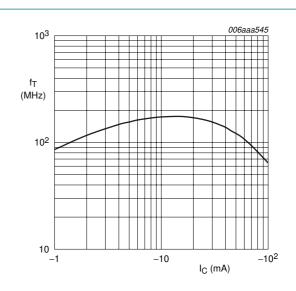
Fig 4. Collector-emitter saturation voltage as a function of collector current; typical values

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 $V_{CE} = -5 \text{ V}; T_{amb} = 25 \, ^{\circ}\text{C}$

Fig 5. Base-emitter voltage as a function of collector current; typical values



 $V_{CE} = -5 \text{ V}; T_{amb} = 25 \, ^{\circ}\text{C}$

Fig 6. Transition frequency as a function of collector current; typical values

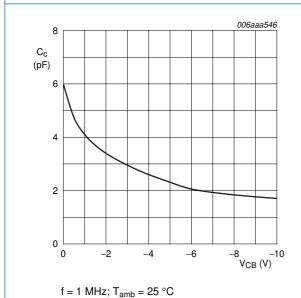
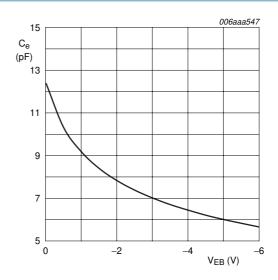


Fig 7. Collector capacitance as a function of

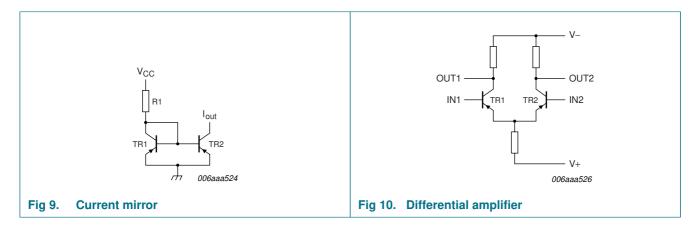
collector-base voltage; typical values



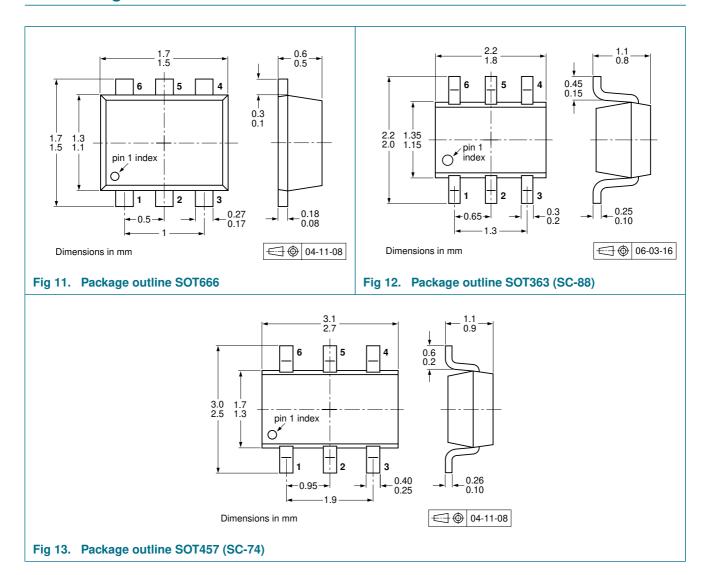
f = 1 MHz; $T_{amb} = 25 \, ^{\circ}\text{C}$

Fig 8. Emitter capacitance as a function of emitter-base voltage; typical values

8. Application information



9. Package outline



BCM857BV_BS_DS_6

10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

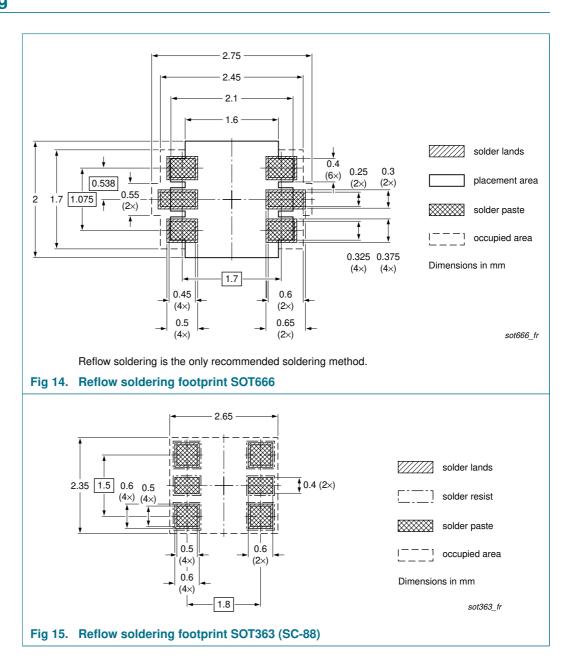
Type number	Package	Description		Packing quantity				
			3000	4000	8000	10000		
BCM857BV SOT666		2 mm pitch, 8 mm tape and reel		-	-	-315	-	
		4 mm pitch, 8 mm tape and reel		-	-115	-	-	
BCM857BS SOT363		4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135	
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165	
BCM857DS	SOT457	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135	
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165	

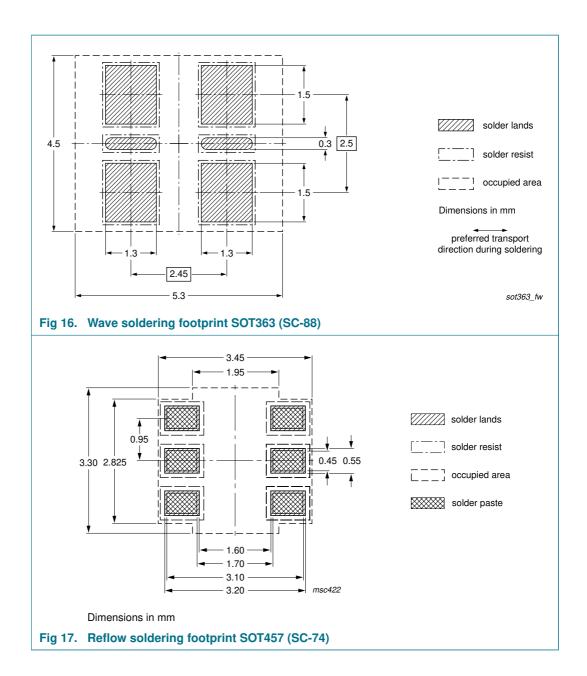
^[1] For further information and the availability of packing methods, see Section 14.

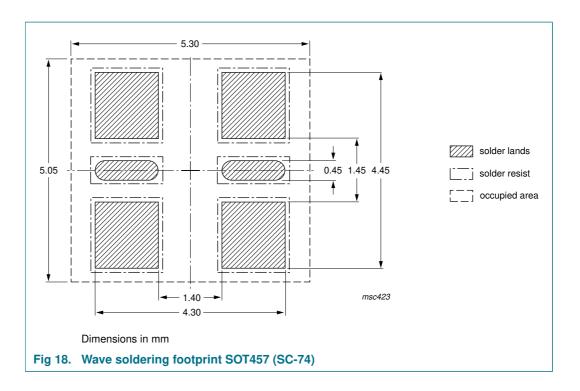
^[2] T1: normal taping

^[3] T2: reverse taping

11. Soldering







12. Revision history

Table 10. Revision history

	-					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
BCM857BV_BS_DS_6	20090828	Product data sheet	-	BCM857BV_BS_DS_5		
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 					
	 Figure 12 "Package outline SOT363 (SC-88)": updated 					
	Figure 14 "Reflow soldering footprint SOT666": updated					
	 Figure 15 "Reflow soldering footprint SOT363 (SC-88)": updated 					
	• Figure 16 "Wave soldering footprint SOT363 (SC-88)": updated					
	• Figure 18 "Wave soldering footprint SOT457 (SC-74)": updated					
BCM857BV_BS_DS_5	20060627	Product data sheet	-	BCM857BS_DS_4		
BCM857BS_DS_4	20060216	Product data sheet	-	BCM857BS_DS_3		
BCM857BS_DS_3	20060130	Product data sheet	-	BCM857BS_2		
BCM857BS_2	20050411	Product data sheet	-	BCM857BS_1		
BCM857BS_1	20040914	Product data sheet	-	-		

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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For sales office addresses, please send an email to: salesaddresses@nxp.com

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BCM857BV/BS/DS

PNP/PNP matched double transistors

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